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Transistors

Power management (dual digital transistors) UMC5N / FMC5A

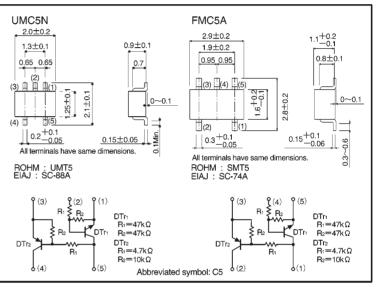
Features

- Both the DTA143X chip and DTZ144E chip in a UMT or SMT package.
- 2) Ideal for power switch circuits.
- Mounting cost and area can be cut in half.

Structure

Epitaxial planar type NPN/PNP silicon transistor (Built-in resistor type)





•Absolute maximum ratings (Ta = 25° C)

Parameter		Symbol	Lin	nits	Unit	
		Symbol	DTr1 (NPN) DTr2 (PNP)		Onit	
Supply voltage		Vcc	50 -50		V	
Input voltage		Vin	40	-20	v	
		VIN	-10	7		
Output current		IO(Max.)	30	-100	mA	
		IC(Max.)	100	100 -100		ША
Power dissipation	UMC5N	Pd	150(TOTAL)		*1 mW *2	
	FMC5A	Fu	300(TOTAL)			
Junction temperature		Tj	150		ĉ	
Storange temperature		Tstg	-55~+150		Ĵ	

*1 120mW per element must not be exceeded.

*2 200mW per element must not be exceeded.

•Electrical characteristics, DTr_1 (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Input voltogo	VI (off)	—	_	0.5	V	Vcc=5V, Io=100 μ A	
Input voltage	$V_{I (on)}$	3	_	—		Vo=0.3V, Io=2mA	
Output voltage	Vo(on)	—	0.1	0.3	V	Io=10mA, I=0.5mA	
Input current	h	—	—	0.18	mA	V1=5V	
Output current	IO (off)	_	_	0.5	μA	Vcc=50V, VI=0V	
DC current gain	Gi	68	_	_	_	Vo=5V, Io=5mA	
Transition frequency	f⊤	_	250	—	MHz	V _{CE} =10mA, I _E =-5mA, f=100MHz *	
Input resistance	R1	32.9	47	61.1	kΩ	_	
Resistance ratio	R2/R1	0.8	1	1.2	—	_	

* Transition frequency of the device

•Electrical characteristics, DTr_2 (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
	VI (off)	_	-	-0.3	v	$V_{CC} = -5V$, $I_0 = -100 \mu A$	
Input voltage	VI (on)	-2.5	—	_		Vo=-0.3V, Io=-20mA	
Output voltage	Vo(on)	—	-0.1	-0.3	V	Io=-10mA, Ii=-0.5mA	
Input current	h	—	—	-1.8	mA	$V_{i}=-5V$	
Output current	IO (off)	—	—	-0.5	μA	$V_{cc} = -50V, V_{l} = 0V$	
DC current gain	Gi	30	—	_	_	$V_0 = -5V$, $I_0 = -10mA$	
Transition frequency	f⊤		250	_	MHz	V _{CE} =-10mA, I _E =5mA, f=100MHz *	
Input resistance	R1	3.29	4.7	6.11	kΩ	—	
Resistance ratio	R2/R1	1.7	2.1	2.6	_	—	

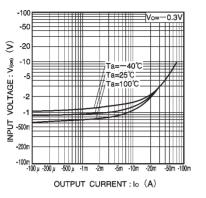
* Transition frequency of the device

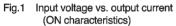
Packaging specifications

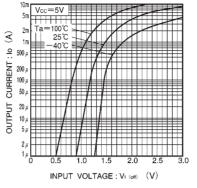
	Packaging type	Taping		
	Code	TR	T148	
Part No.	Basic ordering unit (pieces)	3000	3000	
UMC5N		0	—	
FMC5A			0	

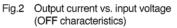


Electrical characteristic curves DTr₁ (NPN)

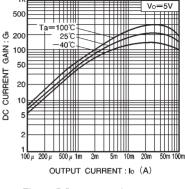








DTr₂ (PNP)



1k

Fig.3 DC current gain vs. output current

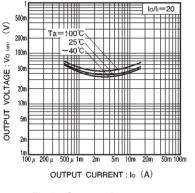


Fig.4 Output voltage vs. output current

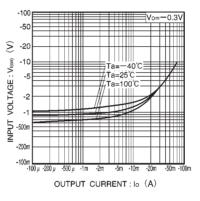


Fig.5 Input voltage vs. output current (ON characteristics)

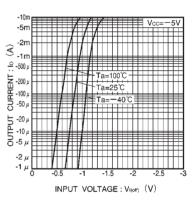


Fig.6 Output current vs. input voltage (OFF characteristics)

